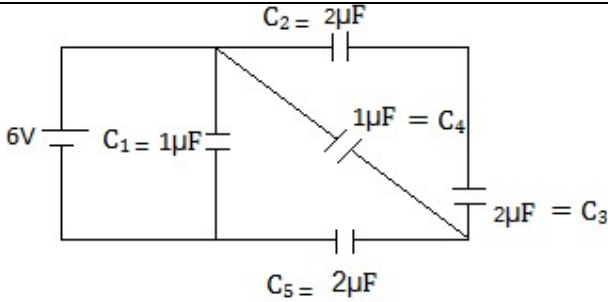


**Class -XII**  
**PHYSICS**  
**SQP Marking Scheme**  
**2019-20**

| Section – A |   |   |
|-------------|---|---|
| 1.          | a, $\phi = \frac{q}{6\epsilon_0}$ (for one face)  | 1 |
| 2.          | b, Conductor  | 1 |
| 3.          | a, $1\Omega$ .  | 1 |
| 4.          | c, 12.0kJ   | 1 |
| 5.          | a, speed  | 1 |
| 6.          | d, virtual and inverted   | 1 |
| 7.          | a, straight line  | 1 |
| 8.          | d, $60^\circ$   | 1 |
| 9.          | b, work function  | 1 |
| 10.         | b, third orbit  | 1 |
| 11.         | $45^\circ$ or vertical  | 1 |
| 12.         | 2 H   | 1 |
| 13.         | double  | 1 |
| 14.         | $1.227 \text{ \AA}$   | 1 |
| 15.         | $60^\circ$  | 1 |
| 16.         | Difference in initial mass energy and energy associated with mass of products<br>Or<br>Total Kinetic energy gained in the process | 1 |
| 17.         | Increases   | 1 |
| 18.         | $N_0/8$   | 1 |
| 19.         | 0.79 eV   | 1 |
| 20.         | Diodes with band gap energy in the visible spectrum range can function as LED   | 1 |

|             |  |                   |
|-------------|--|-------------------|
|             | OR   |                   |
|             | Any one use  |                   |
| Section - B |  |                   |
| 21.         | <p>When electric field E is applied on conductor force acting on free electrons</p> $\vec{F} = -e \vec{E}$ $m\vec{a} = -e \vec{E}$ $\vec{a} = \frac{-e \vec{E}}{m}$ <p>Average thermal velocity of electron in conductor is zero<br/> <math>(u_t)_{av} = 0</math></p> <p>Average velocity of electron in conductors in <math>\tau</math> (relaxation time) = <math>v_d</math> (drift velocity)</p> $v_d = (u_t)_{av} + a \tau$ $v_d = 0 + \frac{-e E \tau}{m}$ $\vec{v}_d = \frac{-e \vec{E} \tau}{m}$   | <p>1</p> <p>1</p> |
| 22.         |  <p> <math>C_2</math> and <math>C_3</math> are in series<br/> <math>\frac{1}{C'} = \frac{1}{2} + \frac{1}{2} = 1</math><br/> <math>C' = 1\mu f</math><br/> <math>C'</math> &amp; <math>C_4</math> are in <math>\parallel</math><br/> <math>C'' = 1 + 1 = 2\mu f</math><br/> <math>C''</math> &amp; <math>C_5</math> are in series<br/> <math>\frac{1}{C'''} = \frac{1}{2} + \frac{1}{2} \Rightarrow C''' = 1\mu f</math><br/> <math>C'''</math> &amp; <math>C_1</math> are in <math>\parallel</math><br/> <math>C_{eq} = 1 + 1 = 2\mu f</math> </p> <p>Energy stored</p> $U = \frac{1}{2} C V^2 = \frac{1}{2} \times 2 \times 10^{-6} \times 6^2$ $= 36 \times 10^{-6} J$ | <p>1</p> <p>1</p> |



$$= 5.17 \times 10^{14} \text{ Hz}$$

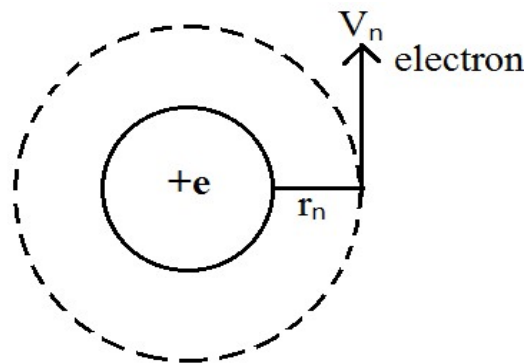
(b) As  $k_{\max} = eV_0 = 0.6\text{eV}$

$$\text{Energy of photon } E = k_{\text{max}} + \omega = 0.6\text{eV} + 2.14\text{eV} = 2.74\text{eV}$$

$$\text{Wave length of photon } \lambda = \frac{hc}{E} = \frac{6.62 \times 10^{-34} \times 3 \times 10^8}{2.74 \times 1.6 \times 10^{-19}} = 4530 \text{ \AA}$$

1

26.



centripetal force = electrostatic attraction

$$\frac{mv_n^2}{r_n} = \frac{1}{4\pi\epsilon_0} \frac{e^2}{r_n^2}$$

$$mv_n^2 = \frac{1}{4\pi\epsilon_0} \frac{e^2}{r_n} \text{-----(i)}$$

$$m\mathbf{v}_n r_n = n \cdot \frac{h}{2\pi}$$

$$V_n = \frac{n\hbar}{2\pi m r_n} \text{ put in (i)}$$

$$m \cdot \frac{n^2 h^2}{4\pi^2 m^2 r_n^3} = \frac{1}{4\pi\epsilon_0} \frac{e^2}{r_n}$$

$$r_n = \frac{\epsilon_0 n^2 h^2}{\pi m e^2}$$

**OR**

Energy of electron in  $n = 2$  is  $-3.4\text{eV}$

$\therefore$  energy in ground state = -13.6eV

$$kE = -TE = +13.6\text{eV}$$

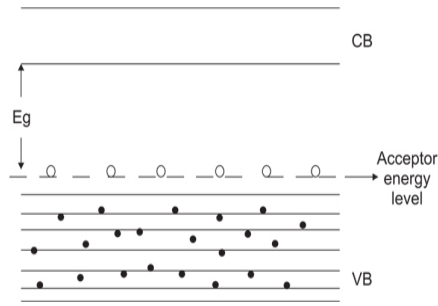
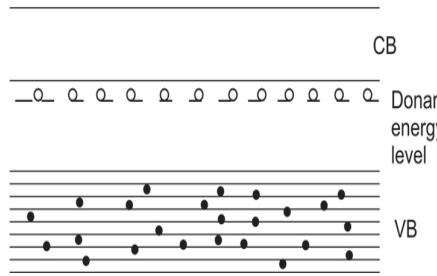
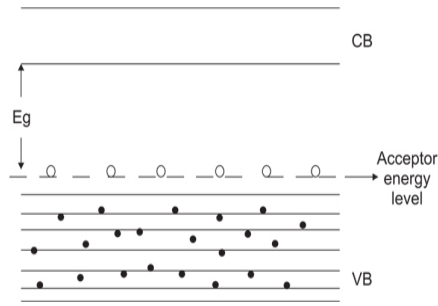
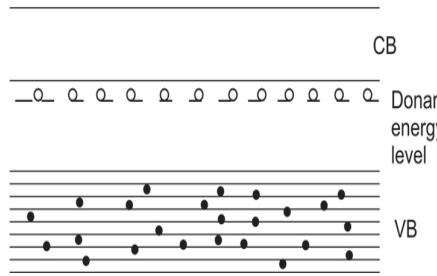
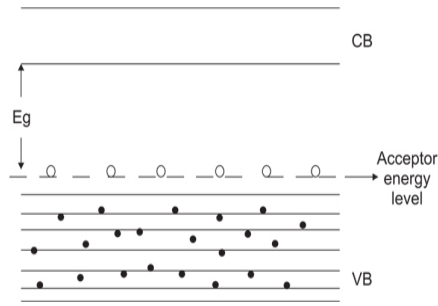
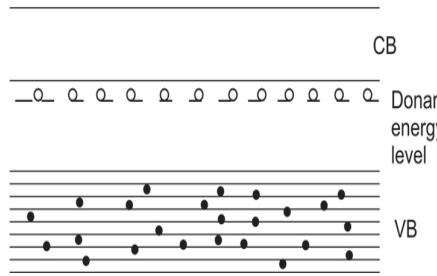
$$E_n = \frac{-13.6 \text{ eV}}{n^2} \Rightarrow -3.4 \text{ eV} = \frac{-13.6 \text{ eV}}{n^2} \Rightarrow$$

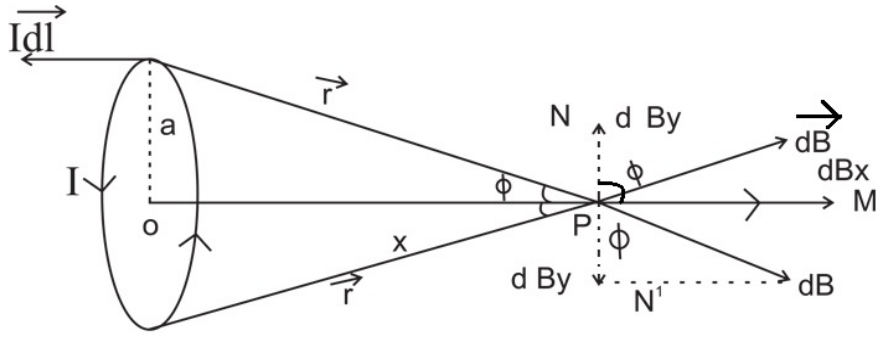
energy in ground state  $x = -13.6\text{eV}$ .

1

1

1

|   | PE = 2TE = -2×13.6eV = -27.2eV  | 1                          |                      |  |  |  |  |   |   |                                     |
|---|---|----------------------------|----------------------|--|--|--|--|---|---|-------------------------------------|
| 27.   | <table> <tr> <th>P-type semiconductor</th> <th>n-type semiconductor</th> </tr> <tr> <td>1. Density of holes &gt;&gt; density of electron</td> <td>1. density of electron&gt;&gt;density of holes</td> </tr> <tr> <td>2. Formed by doping trivalent impurity</td> <td>2. formed by doping pentavalent impurity</td> </tr> <tr> <td>           Energy band diagram for p-type<br/>  </td> <td>           Energy band diagram of n-type semiconductor<br/>  </td> </tr> </table> <p style="text-align: center;"><b>OR</b></p> <p>Energy of photon <math>E = \frac{hc}{\lambda} = \frac{6.62 \times 10^{-34} \times 3 \times 10^8}{6000 \times 10^{-3} \times 1.6 \times 10^{-19}} \text{eV} = 2.06 \text{eV}</math></p> <p>As <math>E &lt; E_g</math> (2.8eV), so photodiode cannot detect this photon.</p> | P-type semiconductor       | n-type semiconductor | 1. Density of holes >> density of electron | 1. density of electron>>density of holes | 2. Formed by doping trivalent impurity | 2. formed by doping pentavalent impurity | Energy band diagram for p-type<br> | Energy band diagram of n-type semiconductor<br> | <p>Any 2x1 =1</p> <p>1</p> <p>1</p> |
| P-type semiconductor  | n-type semiconductor  |                            |                      |  |  |  |  |   |   |                                     |
| 1. Density of holes >> density of electron  | 1. density of electron>>density of holes  |                            |                      |  |  |  |  |   |   |                                     |
| 2. Formed by doping trivalent impurity  | 2. formed by doping pentavalent impurity  |                            |                      |  |  |  |  |   |   |                                     |
| Energy band diagram for p-type<br> | Energy band diagram of n-type semiconductor<br>   |                            |                      |  |  |  |  |   |   |                                     |
| <b><u>Section – C</u></b>   |   |                            |                      |  |  |  |  |   |   |                                     |
| 28.   | <p>Principle of potentiometer, when a constant current flows through a wire of uniform area of cross-section, the potential drop across any length of the wire is directly proportional to the length.</p> <p>Let resistance of wire AB be <math>R_1</math> and its length be 'l' then current drawn from driving cell –</p> $I = \frac{V}{R+R_1} \text{ and hence}$ <p>P.D. across the wire AB will be</p> $V_{AB} = IR_1 = \frac{V}{R+R_1} \times \frac{\rho l}{a}$ <p>Where 'a' is area of cross-section of wire AB</p> $\therefore \frac{V_{AB}}{l} = \frac{V \rho}{(R+R_1).a} = \text{constant} = k$ <p>Where R increases, current and potential difference across wire AB will be</p>   | <p>1</p> <p>1</p> <p>1</p> |                      |  |  |  |  |   |   |                                     |

|     |   |   |
|-----|---|---|
|     | decreased and hence potential gradient 'k' will also be decreased. Thus the null point or balance point will shift to right (towards, B) side.  |   |
| 29. |  <p>According to Biot-Savart's law, magnetic field due to a current element is given by</p> $\overrightarrow{dB} = \frac{\mu_0 I d\vec{l} \times \vec{r}}{4\pi r^2} \text{ where } r = \sqrt{x^2 + a^2}$ $\therefore dB = \frac{\mu_0 I dl \sin 90^\circ}{4\pi (x^2 + a^2)^{3/2}}$ <p>And direction of <math>\overrightarrow{dB}</math> is <math>\perp</math> to the plane containing <math>\overrightarrow{dl}</math> and <math>\vec{r}</math>.</p> <p>Resolving <math>\overrightarrow{dB}</math> along the x - axis and y - axis.</p> $dB_x = dB \sin \theta$ $dB_y = dB \cos \theta$ <p>taking the contribution of whole current loop we get</p> $B_x = \oint dB_x = \oint dB \sin \theta = \int \frac{\mu_0 I dl}{4\pi (x^2 + a^2)^{3/2}} \frac{a}{\sqrt{x^2 + a^2}}$ $B_x = \frac{\mu_0 I a}{4\pi (x^2 + a^2)^{3/2}} \oint dl = \frac{\mu_0 I a \times 2\pi a}{4\pi (x^2 + a^2)^{3/2}}$ <p>And <math>B_y = \oint dB_y = \oint dB \cos \theta = 0</math></p> $\therefore B_P = \sqrt{B_x^2 + B_y^2} = B_x = \frac{\mu_0 2IA}{4\pi (x^2 + a^2)^{3/2}}$ $\therefore \overrightarrow{B_P} = \frac{\mu_0 2m\vec{i}}{4\pi (x^2 + a^2)^{3/2}} (\because \vec{m} = I\vec{A})$ <p>For centre <math>x = 0</math></p> $\therefore  \overrightarrow{B_o}  = \frac{\mu_0 2I\pi a^2}{4\pi a^3} = \mu_0 \left( \frac{I}{2a} \right) \text{ in the direction of } \vec{m}$ | <p>1</p> <p>1/2</p> <p>1/2</p> <p>1</p> |



of light used.

$$D = 100\text{inch} = 2.54 \times 100\text{cm} = 254\text{cm} \\ = 2.54\text{m}$$

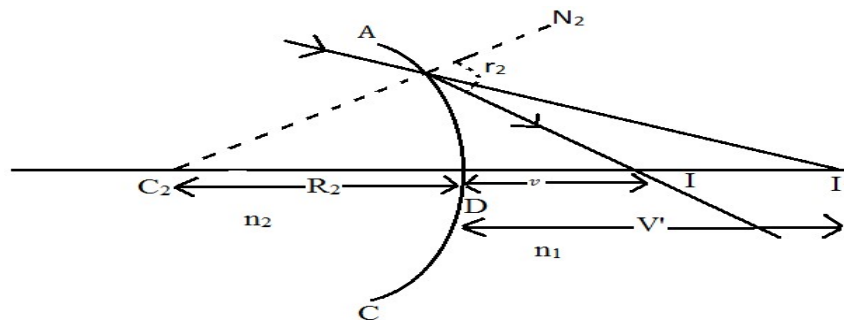
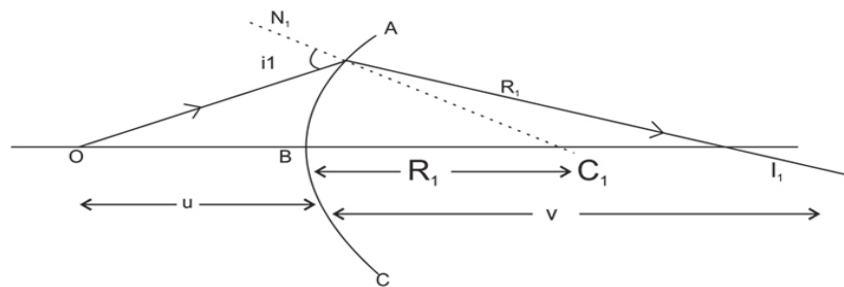
$$\lambda = 6000\text{\AA}$$

$$\text{Limit of resolution } d\theta = \frac{1.22\lambda}{D} \\ = \frac{1.22 \times 6000 \times 10^{-10}\text{m}}{254 \times 10^{-2}\text{m}} \\ = 2.9 \times 10^{-10}$$

OR

Basic assumptions in derivation of Lens-maker's formula:

- (i) Aperture of lens should be small
- (ii) Lenses should be thin
- (iii) Object should be point sized and placed on principal axis.



Suppose we have a thin lens of material of refractive index  $n_2$ , placed in a medium of refractive index  $n_1$ , let o be a point object placed on principle axis then for refraction at surface ABC we get image at  $I_1$ ,

$$\therefore \frac{n_2}{v} - \frac{n_1}{u} = \frac{n_2 - n_1}{R_1} \text{ -----(1)}$$

But the refracted ray before goes to meet at  $I_1$  falls on surface ADC and refracts at  $I_2$

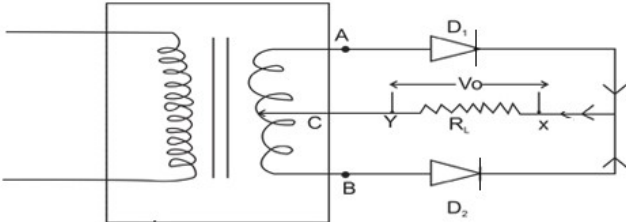
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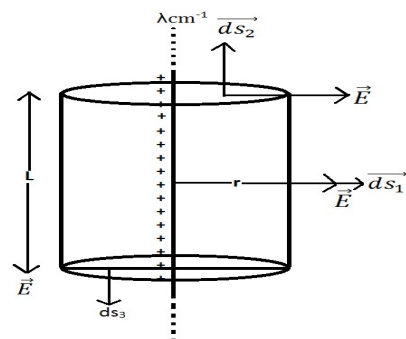
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|     |  |             |
|-----|--|-------------|
|     | <p>finally; hence <math>I_1</math> works as a virtual object 2<sup>nd</sup> refracting surface</p> $\therefore \frac{n_1}{V} - \frac{n_2}{V^1} = \frac{n_2 - n_1}{R_2} \text{ ----- (2)}$ <p>Equation (1) + (2)</p> $\frac{n_1}{V} - \frac{n_1}{u} = (n_2 - n_1) \left( \frac{1}{R_1} - \frac{1}{R_2} \right)$ $\therefore \frac{1}{V} - \frac{1}{u} = (n_{21} - 1) \left( \frac{1}{R_1} - \frac{1}{R_2} \right) \text{ ----- (3)}$ <p>If <math>u = \infty, V = f</math></p> $\frac{1}{f} = (n_{21} - 1) \left( \frac{1}{R_1} - \frac{1}{R_2} \right) \text{ ----- (4)}$ <p>Which is lens maker's formula.</p> | 1           |
| 33. | <p><math>{}^{238}_{92}\text{U} \rightarrow {}^{237}_{91}\text{Pa} + {}^1_1\text{H} + Q</math></p> $\begin{aligned} \because Q &= [M_U - M_{Pa} - M_H] c^2 \\ &= [238.05079 - 237.05121 - 1.00783] \text{ u} \times c^2 \\ &= -0.00825 \text{ u} \times 931.5 \frac{\text{MeV}}{\text{u}} \\ &= -7.68 \text{ MeV} \end{aligned}$ <p><math>\because Q &lt; 0</math> ; therefore it can't proceed spontaneously. We will have to supply energy of 7.68MeV to <math>{}^{238}_{92}\text{U}</math> nucleus to make it emit proton.</p>   | 1<br>1<br>1 |
| 34. | <p>Circuit Diagram</p>  <p>One possible answer: Change the connection of R from point C to point B.</p> <p>Now No Current flowing through <math>D_2</math> in the second half.</p> <p>1 mark for any correct diagram<br/>2 marks for correct explanation</p>  | 1<br><br>2  |

### Section - D

35.  
(a)



1

According to Gauss's law -

$$\oint \vec{E} \cdot d\vec{s} = \frac{1}{\epsilon_0} \{q\}$$

$$\int \vec{E} \cdot d\vec{s}_1 + \int \vec{E} \cdot d\vec{s}_2 + \int \vec{E} \cdot d\vec{s}_3 = \frac{1}{\epsilon_0} (\lambda L)$$

$$\int E ds_1 \cos 0 + \int E ds_2 \cos 90^\circ + \int E ds_3 \cos 90^\circ = \frac{\lambda L}{\epsilon_0}$$

1

$$E \int ds_1 = \frac{\lambda L}{\epsilon_0}$$

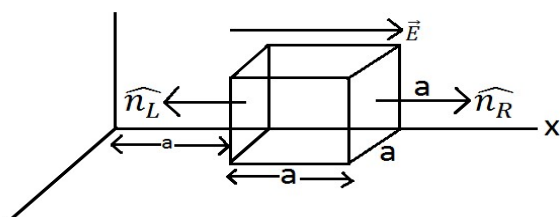
$$E \times 2\pi r L = \frac{\lambda L}{\epsilon_0}$$

$$E = \frac{\lambda}{2\pi\epsilon_0 r}$$

$$\vec{E} = \frac{\lambda}{2\pi\epsilon_0 r} \hat{r}$$

1

35.  
(b)



$$\because E_x = \propto x = 400x$$

$$E_y = E_z = 0$$

Hence flux will exist only on left and right faces of cube as  $E_x \neq 0$

$$\because \vec{E}_L \cdot a^2(\vec{n}_L) + \vec{E}_R \cdot a^2(\vec{n}_R) = \frac{1}{\epsilon_0} \{q_{in}\} = \phi$$

$$-E_L \cdot a^2(\vec{n}_L) + a^2 E_R = \phi_{Net}$$

$$\phi_{Net} = -(400a)a^2 + a^2 (400 \times 2a)$$

$$= -400a^3 + 800a^3$$

$$= 400a^3$$

$$= 400 \times (.1)^3$$

$$\phi_{Net} = 0.4 \text{ Nm}^2\text{C}^{-1}$$

1

$$\therefore \phi_{Net} = \frac{1}{\epsilon_0} \{q_{in}\}$$

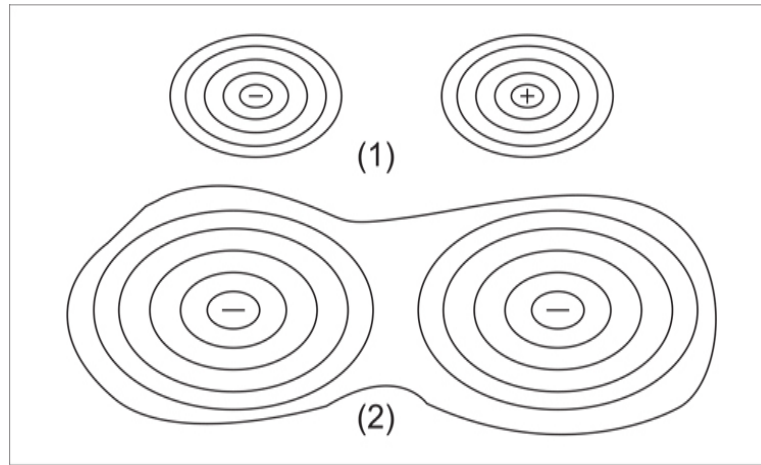
$$\begin{aligned}\therefore q_{in} &= \epsilon_0 \phi_{Net} \\ &= 8.85 \times 10^{-12} \times 0.4 \\ &= 3.540 \times 10^{-12} \text{C}\end{aligned}$$

**OR**

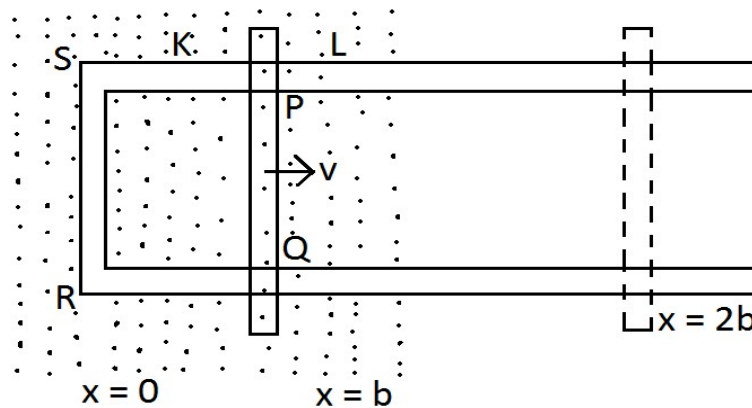
- (a) Definition of electrostatic potential – SI unit J/c of Volt.  
Deduction of expression of electrostatic potential energy of given system of charges –

$$U = \frac{1}{4\pi\epsilon_0} \left[ \frac{q_1 q_2}{r_{12}} + \frac{q_1 q_3}{r_{13}} + \frac{q_2 q_3}{r_{23}} \right]$$

(b)



36. For forward motion from  $x = 0$  to  $x = 2b$ .  
The flux  $\phi_B$  linked with circuit SPQR is



$$\begin{aligned}\phi_B &= Blx & 0 \leq x < b \\ &= Blb & b \leq x < 2b\end{aligned}$$

The induced emf is,

$$e = -\frac{d\phi_B}{dt}$$

$$\begin{aligned}e &= -Blv & 0 \leq x < b \\ &= 0 & b \leq x < 2b\end{aligned}$$

When induced emf is non-zero, the current  $i$  in the magnitude;

$$I = \frac{e}{r} = \frac{Blv}{r}$$

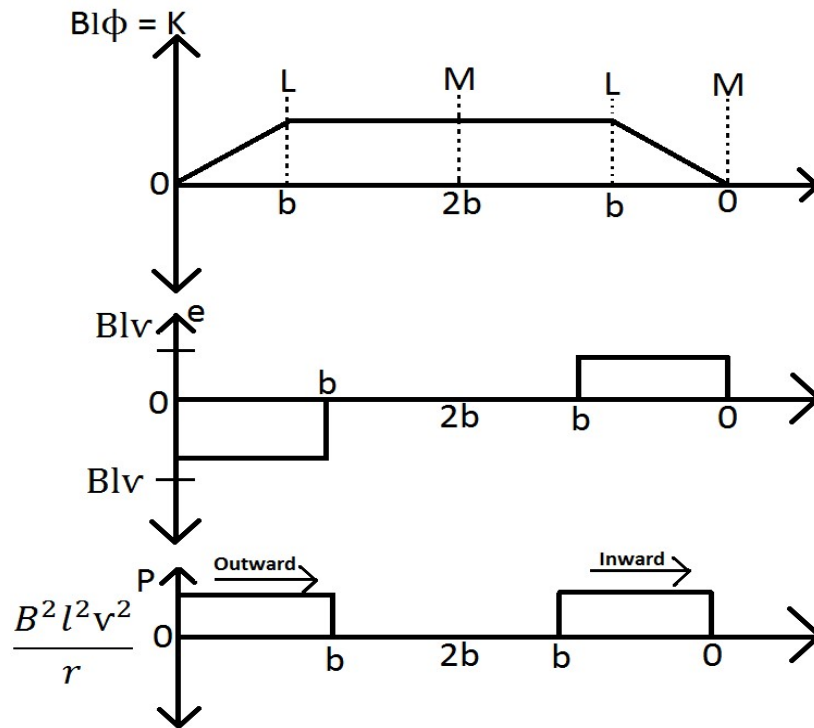
The force required to keep arm PQ in constant motion is  $F = IlB$ . Its direction is to the left. In magnitude

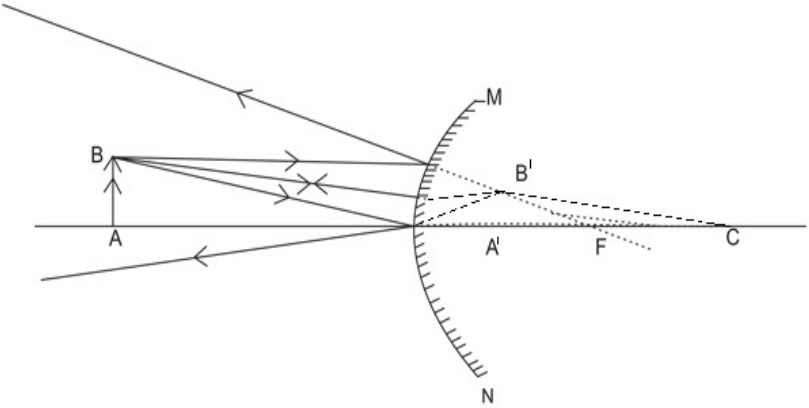
$$\begin{aligned}F &= IlB = \frac{B^2 l^2 v}{r} ; & 0 \leq x < b \\ &= 0 ; & b \leq x < 2b\end{aligned}$$

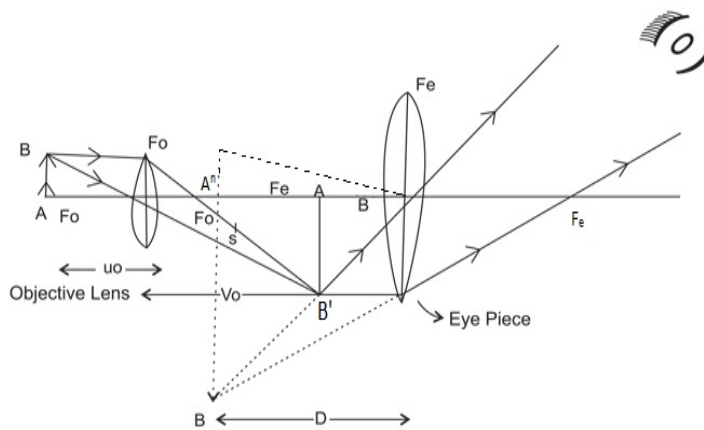
The Joule heating loss is

$$\begin{aligned}P_J &= I^2 r \\ &= \frac{B^2 l^2 v^2}{r} & 0 \leq x < b \\ &= 0 & b \leq x < 2b\end{aligned}$$

One obtains similar expressions for the inward motion from  $x = 2b$  to  $x = 0$



|            |  |                                     |
|------------|--|-------------------------------------|
|            | <p style="text-align: center;"><b><u>OR</u></b></p> <p>Working principle of cyclotron</p> <p>Diagram</p> <p>Working of cyclotron with explanation</p> <p>Any two applications</p>  | <p>1</p> <p>1</p> <p>2</p> <p>1</p> |
| 37.        | <div style="text-align: center;">  </div> <p>Deduction of mirror formula</p> $\frac{1}{v} + \frac{1}{u} = \frac{1}{f}$ <p>For a convex mirror f is always +ve.</p> $\therefore f > c$ <p>Object is always placed in front of mirror hence <math>u &lt; 0</math> (for real object)</p> $\frac{1}{v} + \frac{1}{u} = \frac{1}{f}$ $\Rightarrow \frac{1}{v} = \frac{1}{f} - \frac{1}{u}$ <p>As <math>u &lt; 0</math> u -ve hence</p> $\frac{1}{v} > 0$ $\Rightarrow v > 0 \text{ i.e. +ve for all values of } u.$ <p>Image will be formed behind the mirror and it will be virtual for all values of u.</p> | <p>1</p> <p>2</p> <p>1</p> <p>1</p> |
| 37.<br>(a) | <p style="text-align: center;"><b><u>OR</u></b></p> <p>Ray Diagram : (with proper labeling)</p>  | <p>1</p>                            |



$$\text{Magnifying power } m = \frac{V_o}{u_o} \left( 1 + \frac{D}{f_e} \right)$$

$$m = \frac{L}{f_o} \left( 1 + \frac{D}{f_e} \right)$$

1

37.  
(b)

$\therefore m = m_o m_e = -30$  (virtual, inverted)

$$\therefore f_o = 1.25 \text{ cm}$$

$$f_e = 5.0 \text{ cm}$$

Let us setup a compound microscope such that the final image be formed at D, then

$$m_e = 1 + \frac{v_e}{f_e} = 1 + \frac{25}{5} = 6$$

and position of object for this image formation can be calculated –

$$\frac{1}{v_e} - \frac{1}{u_e} = \frac{1}{f_e}$$

$$\frac{1}{-25} - \frac{1}{u_e} = \frac{1}{5}$$

$$- \frac{1}{u_e} = \frac{1}{5} + \frac{1}{25} = \frac{6}{25}$$

$$u_e = \frac{-25}{6} = -4.17 \text{ cm.}$$

$$\therefore m = m_o \times m_e$$

$$\therefore m_o = \frac{+V_o}{u_o} = \frac{-30}{6} = -5$$

$$\therefore V = -5u_o$$

$$\frac{1}{v_o} - \frac{1}{u_o} = \frac{1}{f_o}$$

$$\frac{1}{-5u_o} - \frac{1}{u_o} = \frac{1}{1.25}$$

1

1

|  |   |   |
|--|---|---|
|  | $\frac{-f}{5u_o} = \frac{1}{1.25}$ $u_o = -1.5\text{cm} \Rightarrow v_o = 7.5\text{cm}$ <p>Tube length = <math>V_o +  u_e  = 7.5\text{cm} + 4.17\text{cm}</math></p> $L = 11.67\text{cm}$ <p>Object should be placed at 1.5cm distance from the objective lens.</p> | 1 |
|--|---|---|